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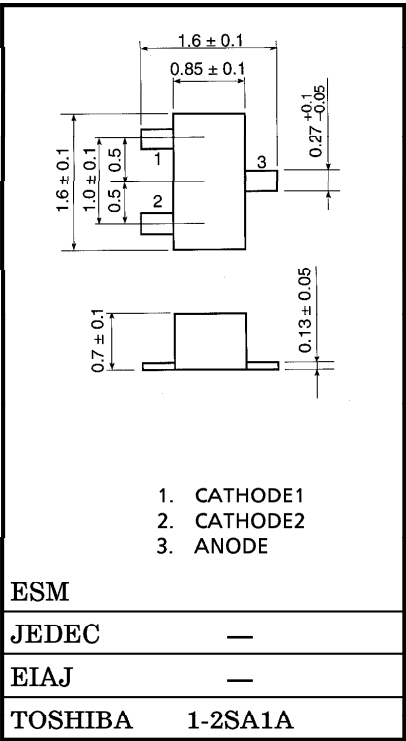
DIODES FOR PROTECTING AGAINST ESD

Unit in mm

- Because two devices are mounted on an ultra compact package, it is possible to allow reducing the number of the parts and the mounting cost.

MAXIMUM RATINGS (Ta = 25°C)

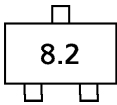
CHARACTERISTIC	SYMBOL	RATING	UNIT
Power Dissipation	P	100	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C



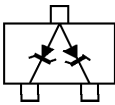
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Zener Voltage	V _Z	I _Z = 5mA	7.7	8.2	8.7	V
Dynamic Impedance	Z _Z	I _Z = 5mA	—	15	—	Ω
Knee Dynamic Impedance	Z _{ZK}	I _Z = 0.5mA	—	20	—	Ω
Reverse Current	I _R	V _R = 6.5V	—	—	0.5	μA

MARKING



EQUIVALENT CIRCUIT (TOP VIEW)



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